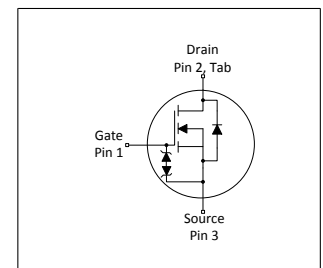
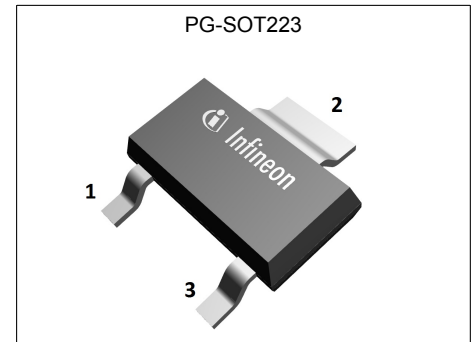


## MOSFET

### 600V CoolMOS™ P7 Power Transistor

The CoolMOS™ 7th generation platform is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. The 600V CoolMOS™ P7 series is the successor to the CoolMOS™ P6 series. It combines the benefits of a fast switching SJ MOSFET with excellent ease of use, e.g. very low ringing tendency, outstanding robustness of body diode against hard commutation and excellent ESD capability. Furthermore, extremely low switching and conduction losses make switching applications even more efficient, more compact and much cooler.



### Features

- Suitable for hard and soft switching (PFC and LLC) due to an outstanding commutation ruggedness
- Significant reduction of switching and conduction losses
- Excellent ESD robustness >2kV (HBM) for all products
- Better  $R_{DS(on)}/package$  products compared to competition enabled by a low  $R_{DS(on)} \cdot A$  (below  $10\text{Ohm} \cdot \text{mm}^2$ )
- Product validation acc. JEDEC Standard

### Benefits

- Ease of use and fast design-in through low ringing tendency and usage across PFC and PWM stages
- Simplified thermal management due to low switching and conduction losses
- Increased power density solutions enabled by using products with smaller footprint and higher manufacturing quality due to >2 kV ESD protection
- Suitable for a wide variety of applications and power ranges



### Potential applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	360	m $\Omega$
$Q_{g,typ}$	13	nC
$I_{D,pulse}$	26	A
$E_{oss} @ 400V$	1.6	$\mu\text{J}$
Body diode $di_f/dt$	900	A/ $\mu\text{s}$

Type / Ordering Code	Package	Marking	Related Links
IPN60R360P7S	PG-SOT223	60S360	see Appendix A

## Table of Contents

Description .....	1
Maximum ratings .....	3
Thermal characteristics .....	4
Electrical characteristics .....	5
Electrical characteristics diagrams .....	7
Test Circuits .....	11
Package Outlines .....	12
Appendix A .....	13
Revision History .....	14
Trademarks .....	14
Disclaimer .....	14

## 1 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	9 6	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	26	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	27	mJ	$I_D=2.5\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche energy, repetitive	$E_{AR}$	-	-	0.14	mJ	$I_D=2.5\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10
Avalanche current, single pulse	$I_{AS}$	-	-	2.5	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	80	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	$V_{GS}$	-20	-	20	V	static;
Gate source voltage (dynamic)	$V_{GS}$	-30	-	30	V	AC ( $f>1\text{ Hz}$ )
Power dissipation	$P_{tot}$	-	-	7	W	$T_C=25^\circ\text{C}$
Storage temperature	$T_{stg}$	-40	-	150	$^\circ\text{C}$	-
Operating junction temperature	$T_j$	-40	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	-	Ncm	-
Continuous diode forward current	$I_S$	-	-	9	A	$T_C=25^\circ\text{C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	26	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 9\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di <sub>f</sub> /dt	-	-	900	A/ $\mu\text{s}$	$V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 9\text{A}$ , $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	$V_{ISO}$	-	-	n.a.	V	$V_{rms}$ , $T_C=25^\circ\text{C}$ , $t=1\text{min}$

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum Duty Cycle  $D = 0.50$ ; DPAK / IPAK equivalent.

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_\theta$

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - solder point	$R_{thJS}$	-	-	17.4	°C/W	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	160	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	$R_{thJA}$	-	35	75	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm <sup>2</sup> (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	reflow MSL1

### 3 Electrical characteristics

at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{V}$ , $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$ , $I_D=0.14\text{mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^\circ\text{C}$ $V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=150^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-	1000	nA	$V_{GS}=20\text{V}$ , $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.300 0.702	0.360 -	$\Omega$	$V_{GS}=10\text{V}$ , $I_D=2.7\text{A}$ , $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$ , $I_D=2.7\text{A}$ , $T_j=150^\circ\text{C}$
Gate resistance	$R_G$	-	6.2	-	$\Omega$	$f=1\text{MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	555	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Output capacitance	$C_{oss}$	-	10	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=400\text{V}$ , $f=250\text{kHz}$
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	20	-	pF	$V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	214	-	pF	$I_D=\text{constant}$ , $V_{GS}=0\text{V}$ , $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	8	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=2.7\text{A}$ , $R_G=10.0\Omega$ ; see table 9
Rise time	$t_r$	-	7	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=2.7\text{A}$ , $R_G=10.0\Omega$ ; see table 9
Turn-off delay time	$t_{d(off)}$	-	42	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=2.7\text{A}$ , $R_G=10.0\Omega$ ; see table 9
Fall time	$t_f$	-	10	-	ns	$V_{DD}=400\text{V}$ , $V_{GS}=13\text{V}$ , $I_D=2.7\text{A}$ , $R_G=10.0\Omega$ ; see table 9

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{GS}$	-	3	-	nC	$V_{DD}=400\text{V}$ , $I_D=2.7\text{A}$ , $V_{GS}=0$ to 10V
Gate to drain charge	$Q_{gd}$	-	4	-	nC	$V_{DD}=400\text{V}$ , $I_D=2.7\text{A}$ , $V_{GS}=0$ to 10V
Gate charge total	$Q_g$	-	13	-	nC	$V_{DD}=400\text{V}$ , $I_D=2.7\text{A}$ , $V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	5.2	-	V	$V_{DD}=400\text{V}$ , $I_D=2.7\text{A}$ , $V_{GS}=0$ to 10V

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0V, I_F=2.7A, T_j=25^\circ C$
Reverse recovery time	$t_{rr}$	-	145	-	ns	$V_R=400V, I_F=1A, di_F/dt=100A/\mu s$ ; see table 8
Reverse recovery charge	$Q_{rr}$	-	0.74	-	$\mu C$	$V_R=400V, I_F=1A, di_F/dt=100A/\mu s$ ; see table 8
Peak reverse recovery current	$I_{rrm}$	-	11	-	A	$V_R=400V, I_F=1A, di_F/dt=100A/\mu s$ ; see table 8

### 4 Electrical characteristics diagrams

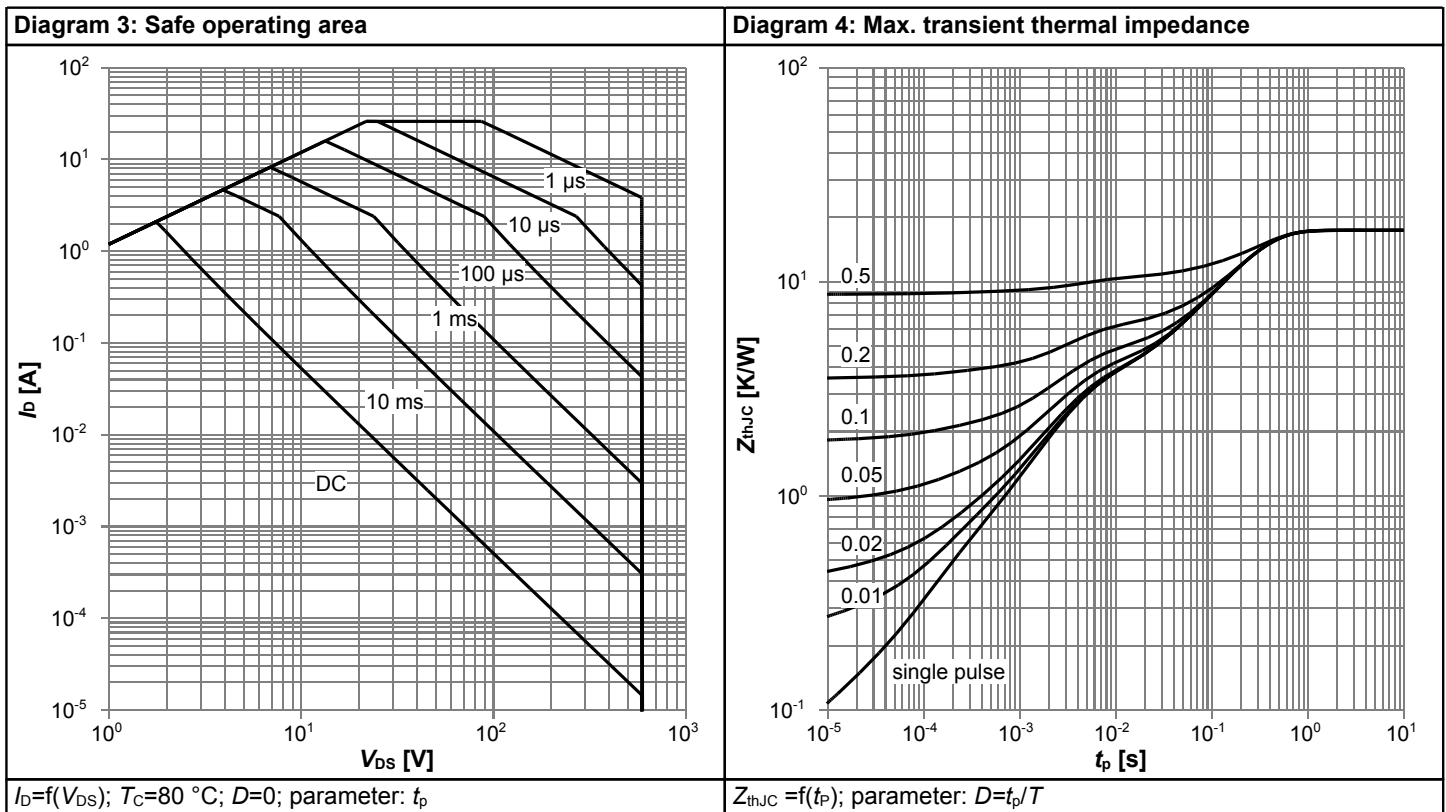
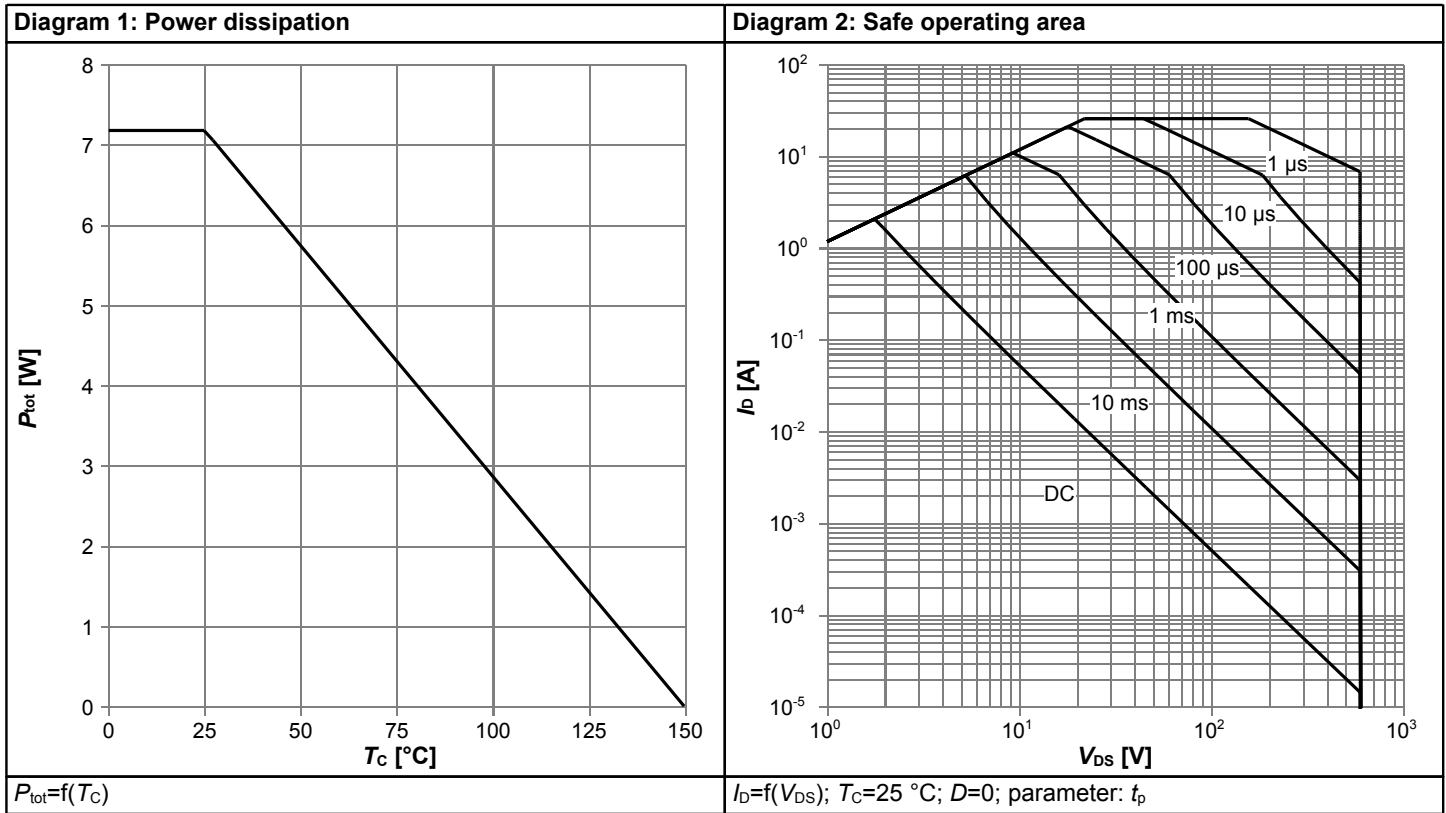
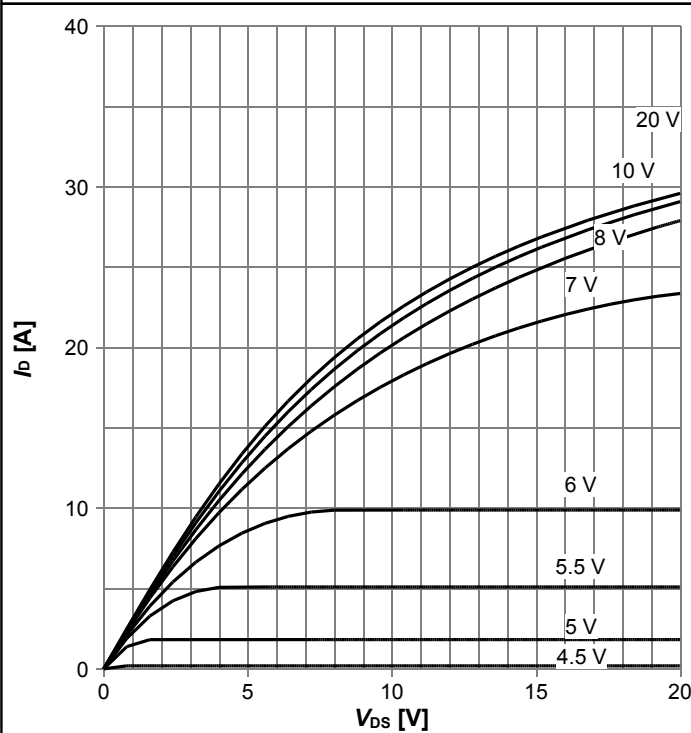
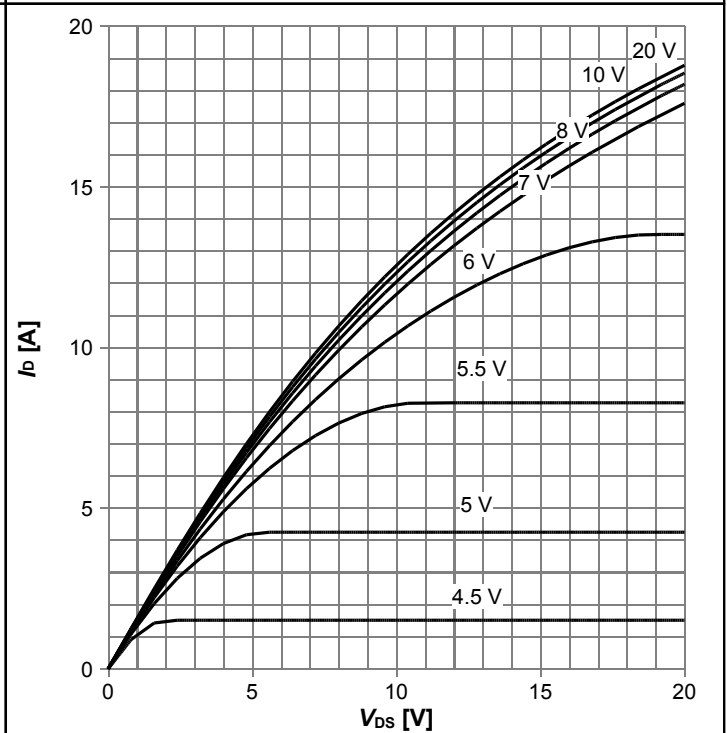


Diagram 5: Typ. output characteristics



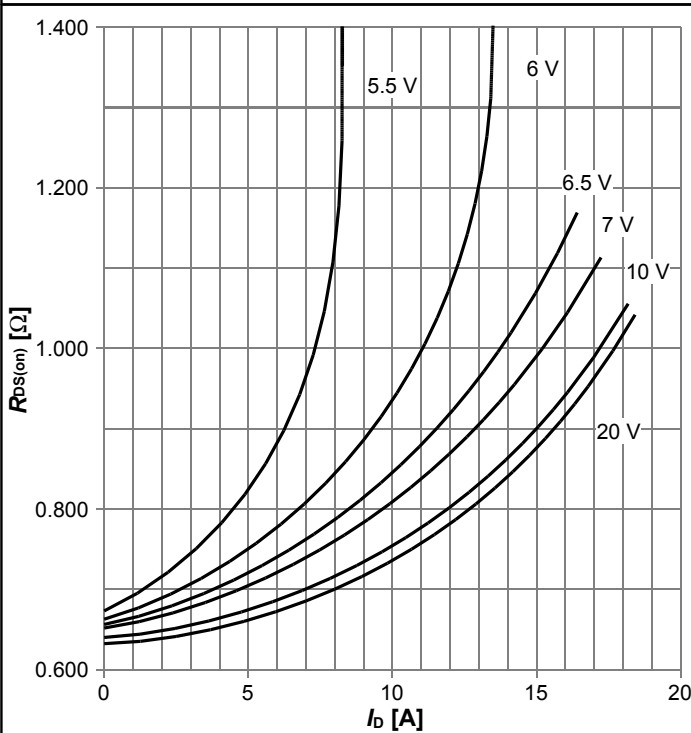
$I_D=f(V_{DS})$ ;  $T_j=25\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. output characteristics



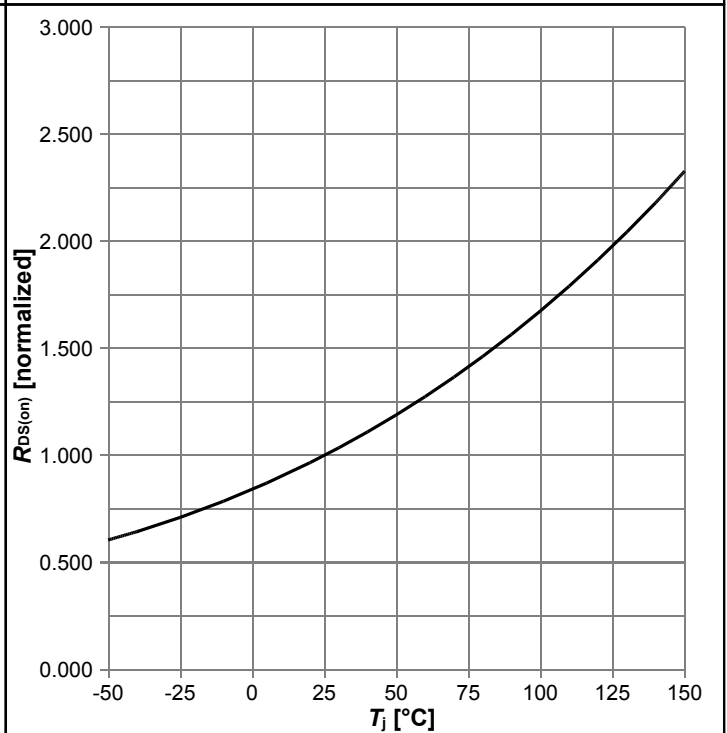
$I_D=f(V_{DS})$ ;  $T_j=125\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D)$ ;  $T_j=125\text{ °C}$ ; parameter:  $V_{GS}$

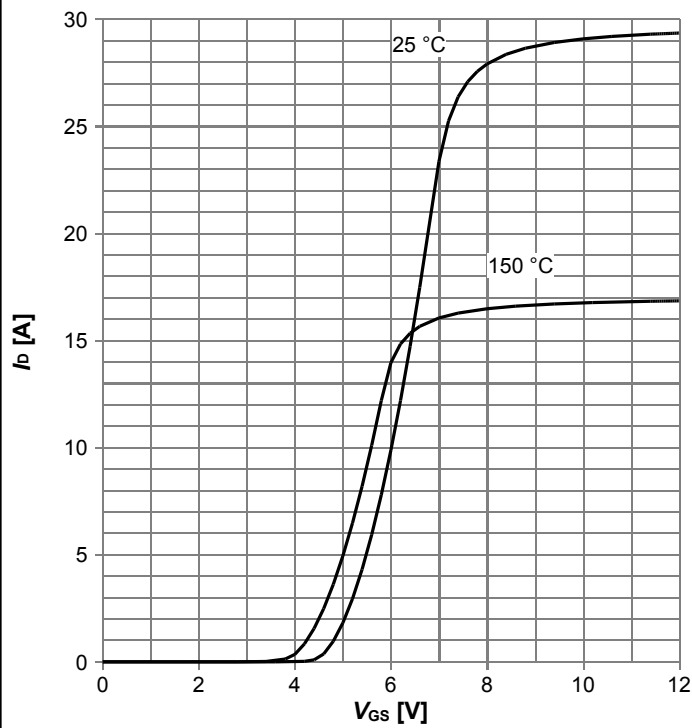
Diagram 8: Drain-source on-state resistance



$R_{DS(on)}=f(T_j)$ ;  $I_D=2.7\text{ A}$ ;  $V_{GS}=10\text{ V}$

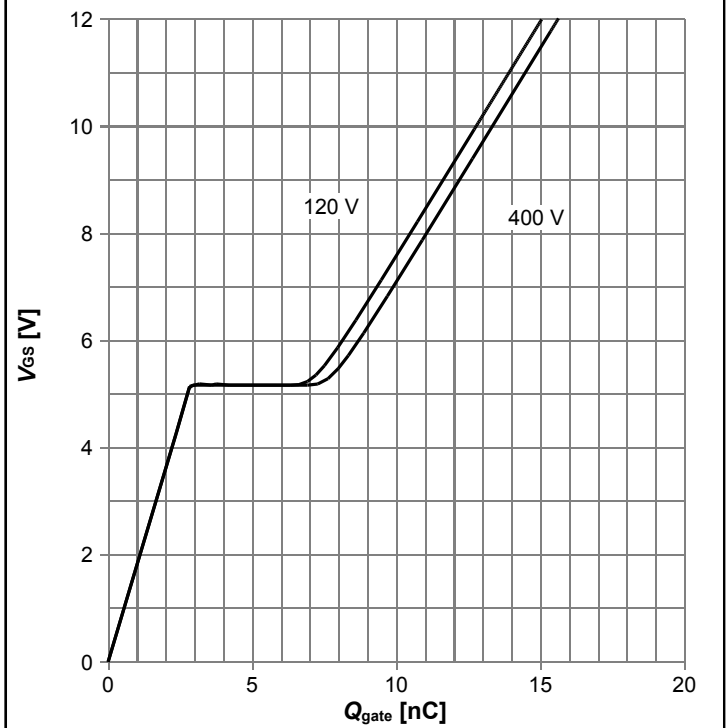


**Diagram 9: Typ. transfer characteristics**



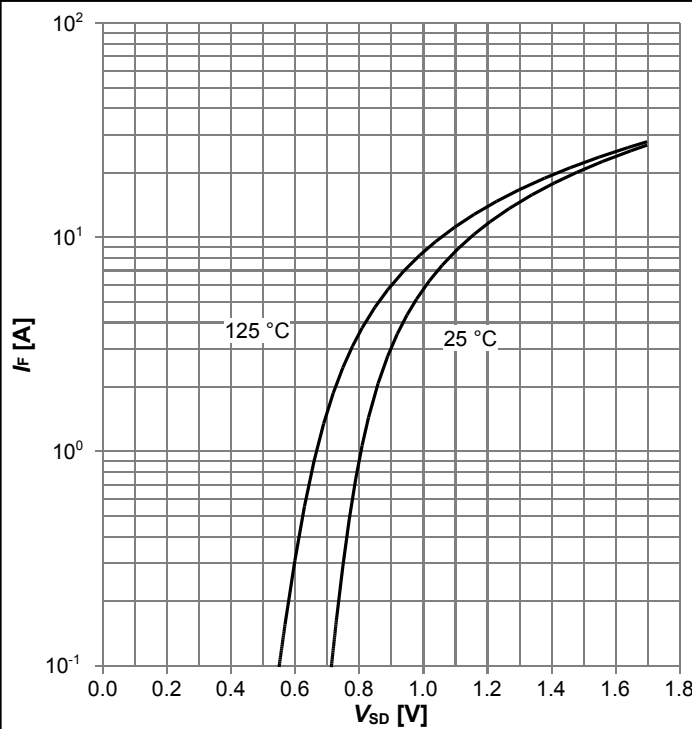
$I_D=f(V_{GS}); V_{DS}=20V; \text{parameter: } T_j$

**Diagram 10: Typ. gate charge**



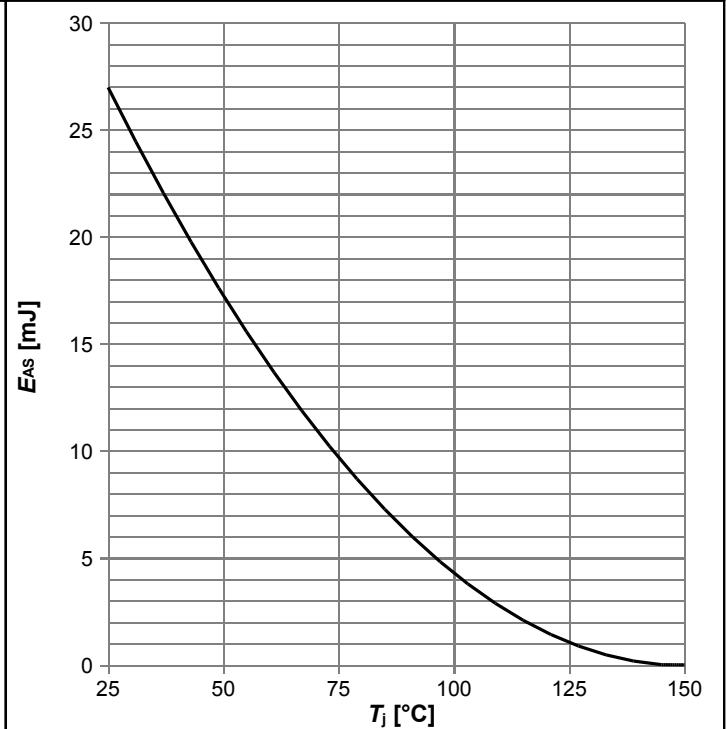
$V_{GS}=f(Q_{gate}); I_D=2.7 \text{ A pulsed}; \text{parameter: } V_{DD}$

**Diagram 11: Forward characteristics of reverse diode**



$I_F=f(V_{SD}); \text{parameter: } T_j$

**Diagram 12: Avalanche energy**



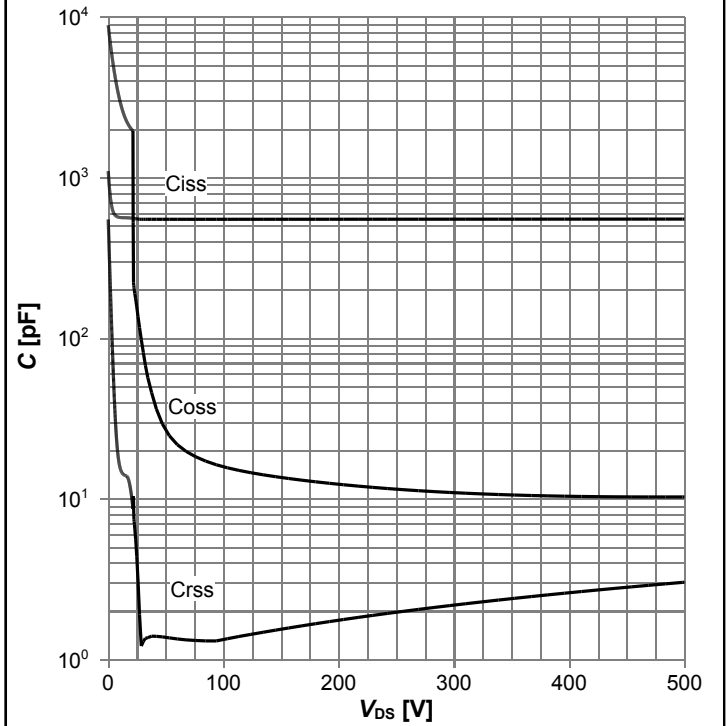
$E_{AS}=f(T_j); I_D=2.5 \text{ A}; V_{DD}=50 \text{ V}$

**Diagram 13: Drain-source breakdown voltage**



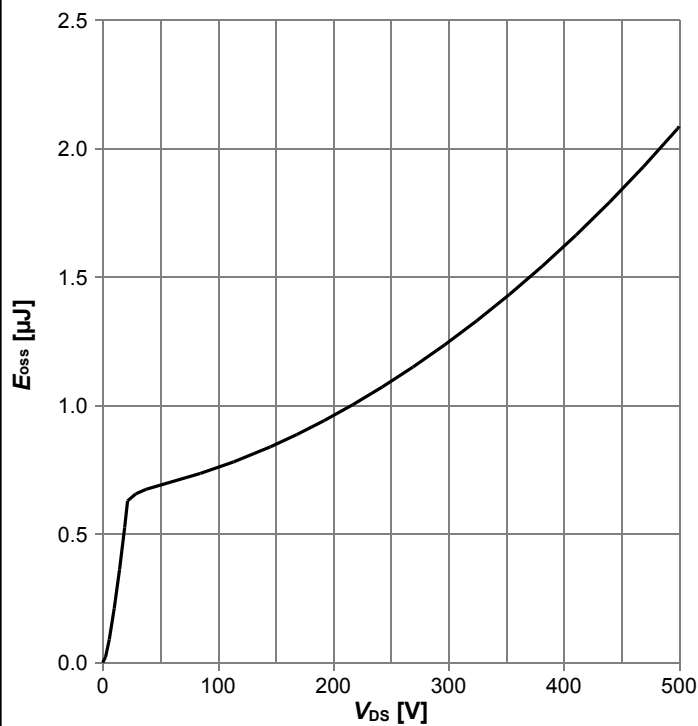
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram 14: Typ. capacitances**



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=250 \text{ kHz}$

**Diagram 15: Typ. Coss stored energy**



$E_{oss}=f(V_{DS})$

## 5 Test Circuits

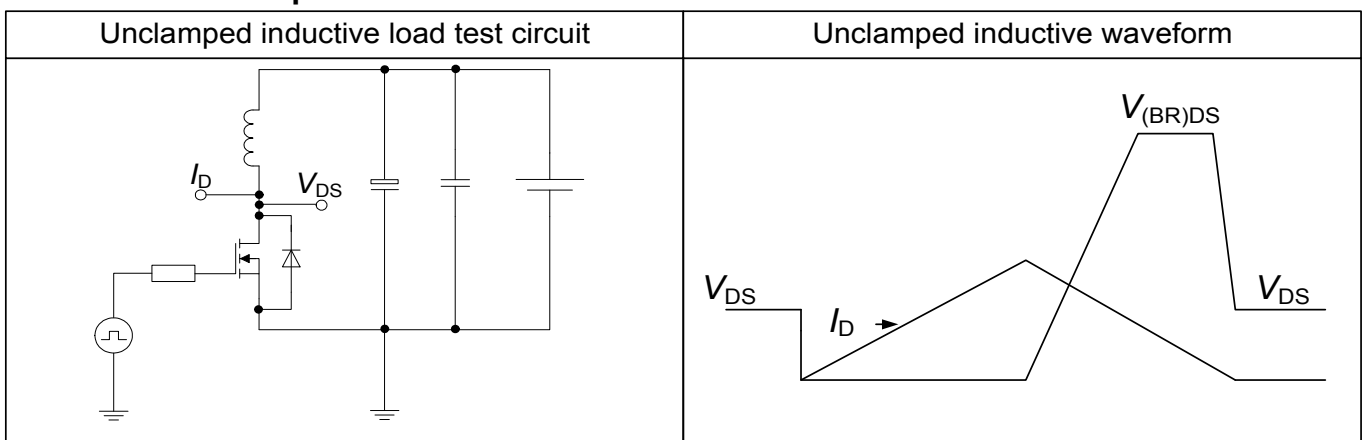
**Table 8 Diode characteristics**



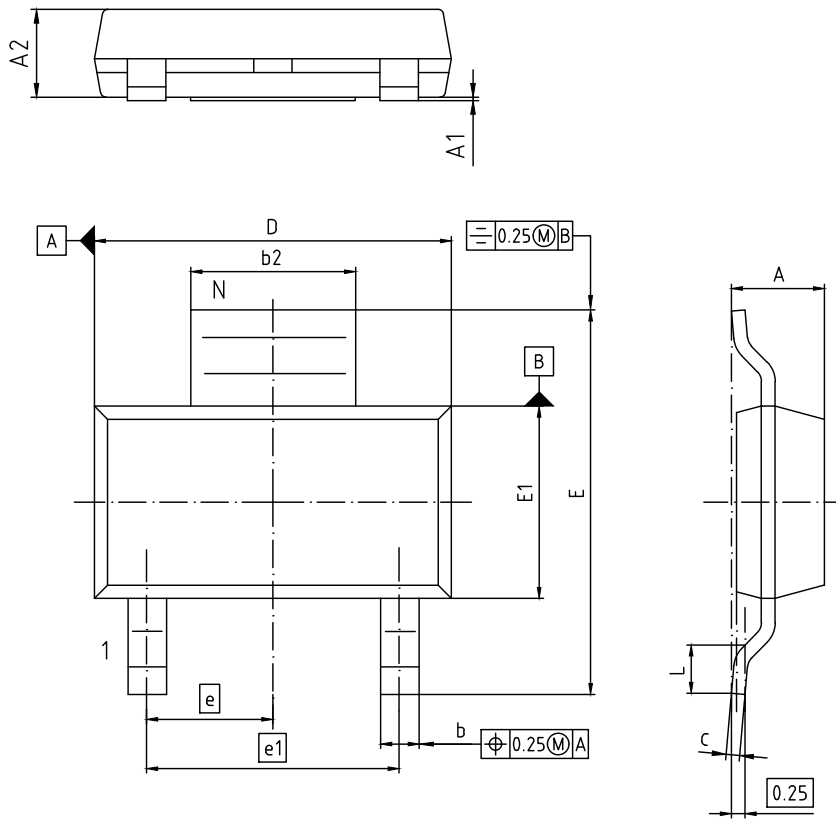
**Table 9 Switching times**



**Table 10 Unclamped inductive load**



## 6 Package Outlines



NOTES:  
1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-261

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.52	1.80	0.060	0.071
A1	-	0.10	-	0.004
A2	1.50	1.70	0.059	0.067
b	0.60	0.80	0.024	0.031
b2	2.95	3.10	0.116	0.122
c	0.24	0.32	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.3 BASIC		0.091 BASIC	
e1	4.6 BASIC		0.181 BASIC	
L	0.75	1.10	0.030	0.043
N	3		3	
O	0°	10°	0°	10°

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Figure 1 Outline PG-SOT223, dimensions in mm/inches

## 7 Appendix A

### Table 11 Related Links

- IFX CoolMOS P7 Webpage: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS P7 application note: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS P7 simulation model: [www.infineon.com](http://www.infineon.com)
- IFX Design tools: [www.infineon.com](http://www.infineon.com)

### Revision History

IPN60R360P7S

**Revision: 2018-04-25, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2017-06-23	Release of final version
2.1	2018-04-25	Updated diagram scalings; Nomenclature of product qualification grade was changed

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